

pervoskite material, where an electric field in the dielectric layer controls a conductivity of the semiconductor substrate.

*Claims 2-8 are unchanged by this Amendment.*

*Please enter new claim 9, as shown immediately hereafter.*

9. A transistor, comprising:

a substrate;

a gate electrode disposed over the substrate for generating a conduction channel in the substrate in response to a control signal; and

a dielectric formed over the conduction channel, the dielectric including a first layer formed with an amorphous material, a second layer formed with a monocrystalline pervoskite material disposed between the first layer and the gate electrode.

*Claims 10-13 are unchanged by this Amendment.*

#### REMARKS

Reexamination and reconsideration of this application as amended is requested. By this amendment, claims 1 and 9 have been amended, and claims 14-20 have been cancelled. Claims 1-13 remain in the application.

#### TELEPHONE INTERVIEW

Applicants appreciate the telephone interview held on 28 March 2002. The amendment of claims 1 and 9 made herein were discussed and were believed to overcome the cited references. It was understood that Examiner Wilson may conduct another search in view of the amendment.

#### RESTRICTION OF CLAIMS

The Examiner has restricted the claims to Group I (claims 1-13) and Group II (claims 14-20). Applicant previously during a telephone conversation elected Group I, claims 1-13.

#### OBJECTION TO THE TITLE

The Examiner has objected to the title. The title has been amended to that suggested by the Examiner.